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STGB10NB60S STGP10NB60S

16 A, 600 V, low drop IGBT

Features

- Low on-voltage drop (V_{CE(sat)})
- High current capability

Applications

- Light dimmer
- Static relays
- Motor drive

Description

This IGBT utilizes the advanced PowerMESH™ process featuring extremely low on-state voltage drop in low-frequency working conditions (up to 1 kHz).

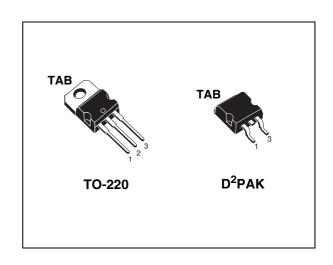


Figure 1. Internal schematic diagram

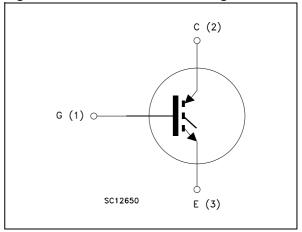


Table 1. Device summary

Order codes	Order codes Marking		Packaging
STGB10NB60ST4	GB10NB60S	D ² PAK	Tape and reel
STGP10NB60S	STGP10NB60S GP10NB60S		Tube

September 2011 Doc ID 10985 Rev 4 1/19

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600	V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	29	Α
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	16	Α
I _{CL} (2)	Turn-off latching current	20	Α
I _{CP} ⁽³⁾	Pulsed collector current	80	Α
V _{GE}	Gate-emitter voltage	± 20	V
P _{TOT}	Total dissipation at T _C = 25 °C	80	W
T _j	Operating junction temperature	– 55 to 150	°C

^{1.} Calculated according to the iterative formula

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

- 2. Vclamp = 80% of V_{CES}, T_j =150 °C, R_G=1k Ω , V_{GE}=15 V
- 3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case	1.56	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

 $(T_j = 25 \, ^{\circ}C \text{ unless otherwise specified})$

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage (V _{GE} = 0)	I _C = 250 μA	600			٧
V _{(BR)ECS}	Emitter-collector breakdown voltage (V _{GE} = 0)	I _C = 1 mA	20			٧
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} = ±20 V			±100	nA
I _{CES}	Collector cut-off current (V _{GE} = 0)	V _{CE} = 600 V V _{CE} = 600 V, T _j = 125 °C			10 100	μ Α μ Α
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}, I_{C} = 250 \mu A$	2.5		5	٧
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 5 A V _{GE} = 15 V, I _C = 10 A V _{GE} = 15 V, I _C = 10 A, T _j = 125 °C		1.15 1.35 1.25	1.75	V
9 _{fs} (1)	Forward transconductance	$V_{CE} = 15 \text{ V}, I_{C} = 10 \text{ A}$	5			S

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0	-	610 65 12	-	pF pF pF
Qg	Total gate charge	$V_{CE} = 400 \text{ V, } I_{C} = 10 \text{ A,}$ $V_{GE} = 15 \text{ V}$ (see Figure 17)		33	1	nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 480 V, I_{C} = 10 A R_{G} = 1 k Ω , V_{GE} = 15 V (see Figure 16)	-	0.7 0.46 8	-	μs μs Α/μs
$t_r(V_{off})$ $t_d(_{off})$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 480 \text{ V}, I_{C} = 10 \text{ A}$ $R_{G} = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V}$ (see Figure 16)	-	2.2 1.2 1.2	-	μs
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 480 \text{ V, } I_{C} = 10 \text{ A}$ $R_{G} = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V,}$ $T_{j} = 125 \text{ °C}$ (see Figure 16)	-	3.8 1.2 1.9	-	μs

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Eon ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 480 V, I_{C} = 10 A R_{G} = 1 k Ω , V_{GE} = 15 V (see Figure 16)	-	0.6 5 5.6	-	mJ mJ mJ
E _{off} ⁽²⁾	Turn-off switching losses	$V_{CC} = 480 \text{ V, } I_{C} = 10 \text{ A}$ $R_{G} = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V,}$ $T_{j} = 125 \text{ °C}$ (see Figure 16)	-	8	-	mJ

Eon is the turn-on losses when a typical diode is used in the test circuit. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature (25°C and 125°C).

^{2.} Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

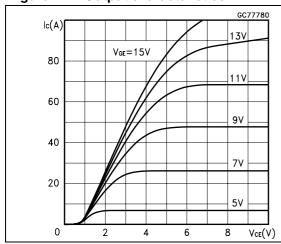


Figure 3. Transfer characteristics

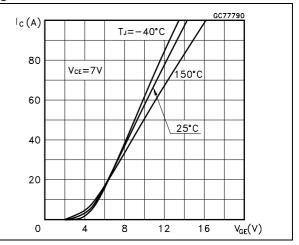
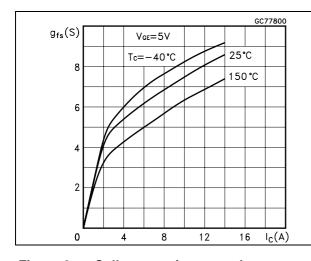


Figure 4. Transconductance

Figure 5. Collector-emitter on voltage vs. temperature



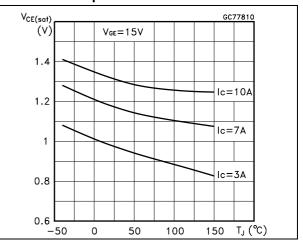
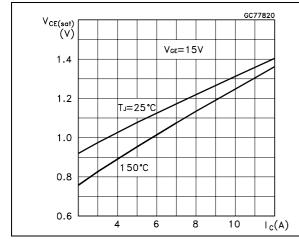
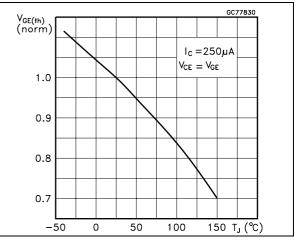


Figure 6. Collector-emitter on voltage vs. collector current

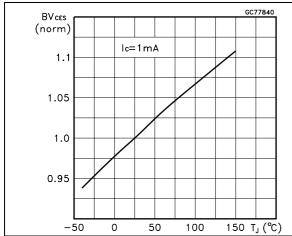
Figure 7. Normalized gate threshold vs. temperature





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Figure 8. Normalized breakdown voltage vs. Figure 9. Gate charge vs. gate-emitter temperature voltage



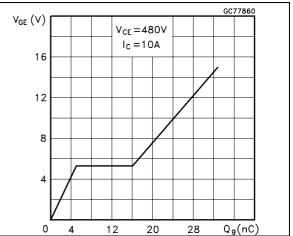


Figure 10. Capacitance variations

GC77850 C(pF) f=1MHz $V_{GE} = 0V$ 800 Cies 600 400 200 Coes Cres 0 5 10 15 20 $V_{CE}(V)$

Figure 11. Switching losses vs. temperature

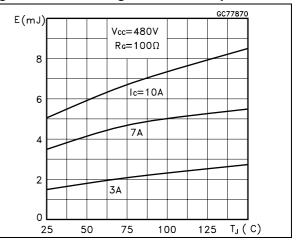
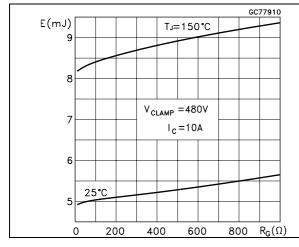
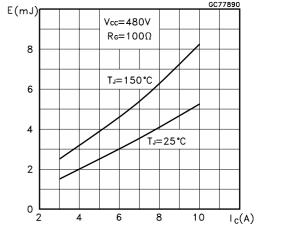


Figure 12. Switching losses vs. gate resistance

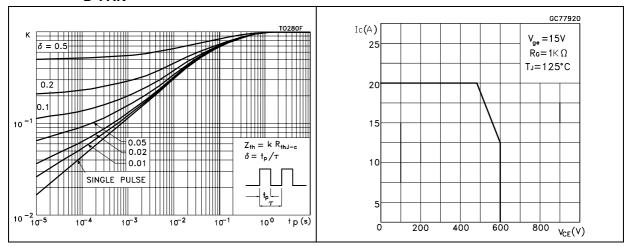
Figure 13. Switching losses vs. collector current





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Figure 14. Thermal impedance for TO-220 and $\,$ Figure 15. Turn-off SOA $\,$ $\,$ D 2 PAK $\,$



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3 Test circuits

Figure 16. Test circuit for inductive load switching

Figure 17. Gate charge test circuit

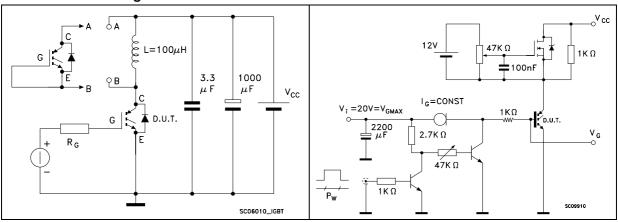
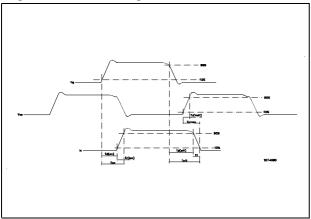


Figure 18. Switching waveforms



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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Table 8. D²PAK (TO-263) mechanical data

	AR (10-200) mechanic	mm	
Dim.	Min.	Тур.	Max.
Α	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
С	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
е		2.54	
e1	4.88		5.28
Н	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

SEATING PLANE

COPLANARITY A1

CAUGE PLANE

V2

0079457_S

Figure 19. D²PAK (TO-263) drawing

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Table 9. TO-220 type A mechanical data

D:		mm.	
Dim.	Min.	Тур.	Max.
Α	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 20. TO-220 type A drawing

5 Packaging mechanical data

Table 10. D²PAK (TO-263) tape and reel mechanical data

	Таре			Reel		
		mm.	Dim	mm.		
Dim.	Min.	Max.	Dim.	Min.	Max.	
A0	10.5	10.7	Α		330	
В0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
Е	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	N	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty	1000	
P2	1.9	2.1		Bulk qty	1000	
R	50					
Т	0.25	0.35				
W	23.7	24.3				

Figure 21. D²PAK footprint ^(a)

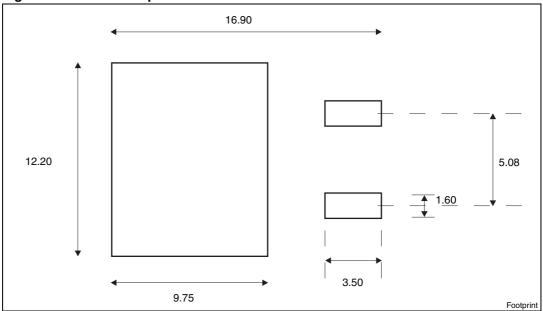
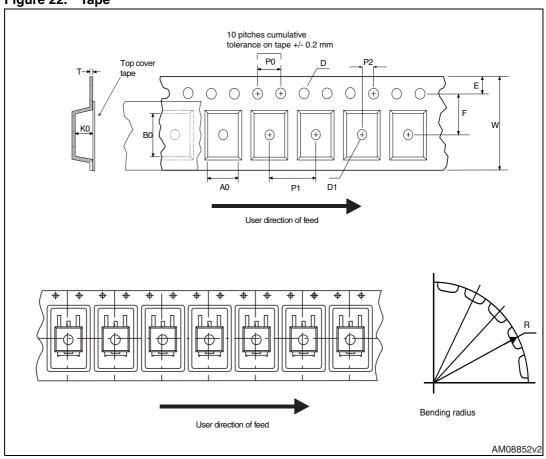
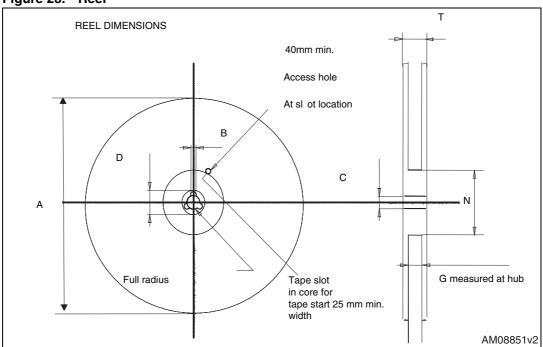


Figure 22. Tape



a. All dimension are in millimeters.

Figure 23. Reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
10-Nov-2004	1	New release.
28-Feb-2005	2	Some values changed in Table 4: Static.
16-Dec-2010	3	Updated <i>Table 2: Absolute maximum ratings</i> . Updated mechanical data <i>Section 4: Package mechanical data</i> .
27-Sep-2011	4	Modified: unit value <i>Table 7 on page 5</i> , <i>Figure 2</i> and <i>Figure 3 on page 6</i> . Updated mechanical data D ² PAK <i>Table 8 on page 11</i> and <i>Figure 19 on page 12</i> . Removed order code STGP10NB60SFP and TO-220FP package mechanical data.

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